DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Information
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Outlines

74HC/HCT4353

Triple 2-channel analog multiplexer/demultiplexer with latch

Product specification
File under Integrated Circuits, IC06

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Philips Semiconductors

PHILIPS

Triple 2-channel analog multiplexer/demultiplexer with latch

74HC/HCT4353

FEATURES

- Wide analog input voltage range: ± 5 V
- Low "ON" resistance:
  80 Ω (typ.) at $V_{CC} - V_{EE}$ = 4.5 V
  70 Ω (typ.) at $V_{CC} - V_{EE}$ = 6.0 V
  60 Ω (typ.) at $V_{CC} - V_{EE}$ = 9.0 V
- Logic level translation:
  to enable 5 V logic to communicate with ± 5 V analog signals
- Typical "break before make" built in
- Address latches provided
- Output capability: non-standard
- I_{CC} category: MSI

GENERAL DESCRIPTION

The 74HC/HCT4353 are high-speed Si-gate CMOS devices. They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT4353 are triple 2-channel analog multiplexers/demultiplexers with two common enable inputs ($\overline{E}_1$ and E_2) and a latch enable input ($\overline{LE}$). Each multiplexer has two independent inputs/outputs (nY_0 and nY_1), a common input/output (nZ) and select inputs (S_1 to S_3).

Each multiplexer/demultiplexer contains two bidirectional analog switches, each with one side connected to an independent input/output (nY_0 and nY_1) and the other side connected to a common input/output (nZ).

With $\overline{E}_1$ LOW and E_2 HIGH, one of the two switches is selected (low impedance ON-state) by S_1 to S_3.
The data at the select inputs may be latched by using the active LOW latch enable input ($\overline{LE}$). When $\overline{LE}$ is HIGH, the latch is transparent. When either of the two enable inputs, $\overline{E}_1$ (active LOW) and E_2 (active HIGH), is inactive, all analog switches are turned off.

V_{CC} and GND are the supply voltage pins for the digital control inputs (S_1 to S_3, $\overline{LE}$, $\overline{E}_1$ and E_2). The V_{CC} to GND ranges are 2.0 to 10.0 V for HC and 4.5 to 5.5 V for HCT. The analog inputs/outputs (nY_0 and nY_1, and nZ) can swing between V_{CC} as a positive limit and V_{EE} as a negative limit. $V_{CC} - V_{EE}$ may not exceed 10.0 V.

For operation as a digital multiplexer/demultiplexer, V_{EE} is connected to GND (typically ground).

QUICK REFERENCE DATA

V_{EE} = GND = 0 V; T_{amb} = 25 °C; $t_r = t_f$ = 6 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC	HCT	
t_{PZH}/ t_{PZL}	turn "ON" time $\overline{E}_1$, E_2 or S_n to V_{os}	C_L = 50 pF; R_L = 1 kΩ; V_{CC} = 5 V	29	21	ns
t_{PHZ}/ t_{PLZ}	turn "OFF" time $\overline{E}_1$, E_2 or S_n to V_{os}		20	22	ns
C_I	input capacitance		3.5	3.5	pF
C_{PD}	power dissipation capacitance per switch	notes 1 and 2	23	23	pF
C_S	max. switch capacitance				
	independent (Y)		5	5	pF
	common (Z)		8	8	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum \{(C_L + C_S) \times V_{CC}^2 \times f_o\}$ where:

   f_i = input frequency in MHz

   C_L = output load capacitance in pF

   f_o = output frequency in MHz

   C_S = max. switch capacitance in pF

   $\sum \{(C_L \times C_S) \times V_{CC}^2 \times f_o\}$ = sum of outputs

   V_{CC} = supply voltage in V

2. For HC the condition is V_I = GND to V_{CC}
   For HCT the condition is V_I = GND to V_{CC} – 1.5 V

ORDERING INFORMATION

See *"74HC/HCT/HCU/HCMOS Logic Package Information"*.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
2, 1	$2Y_0$, $2Y_1$	independent inputs/outputs
5	3Z	common input/output
6, 4	$3Y_0$, $3Y_1$	independent inputs/outputs
3, 14	n.c.	not connected
7	$\overline{E}_1$	enable input (active LOW)
8	E_2	enable input (active HIGH)
9	V_{EE}	negative supply voltage
10	GND	ground (0 V)
11	$\overline{LE}$	latch enable input (active LOW)
15, 13, 12	S_1 to S_3	select inputs
16, 17	$1Y_0$, $1Y_1$	independent inputs/outputs
18	1Z	common input/output
19	2Z	common input/output
20	V_{CC}	positive supply voltage

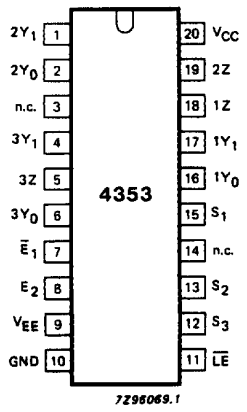


Fig.1 Pin configuration.

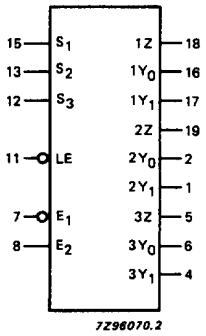


Fig.2 Logic symbol.

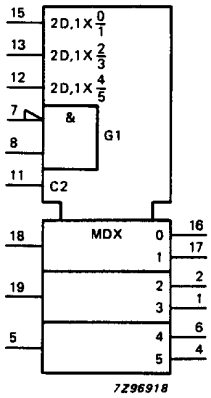


Fig.3 IEC logic symbol.

FUNCTION TABLE

INPUTS				CHANNEL ON
$\overline{E}_1$	E_2	$\overline{LE}$	S_n	
H	H	X	X	none
X	L	X	X	none
L	H	H	L	nY0 – nZ
L	H	H	H	nY_1 – nZ
L	H	L	X	(1)
X	X	↓	X	(2)

Notes

1. Last selected channel “ON”.
2. Selected channels latched.

H = HIGH voltage level
L = LOW voltage level
X = don’t care
↓ = HIGH-to-LOW $\overline{LE}$ transition

APPLICATIONS

- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating

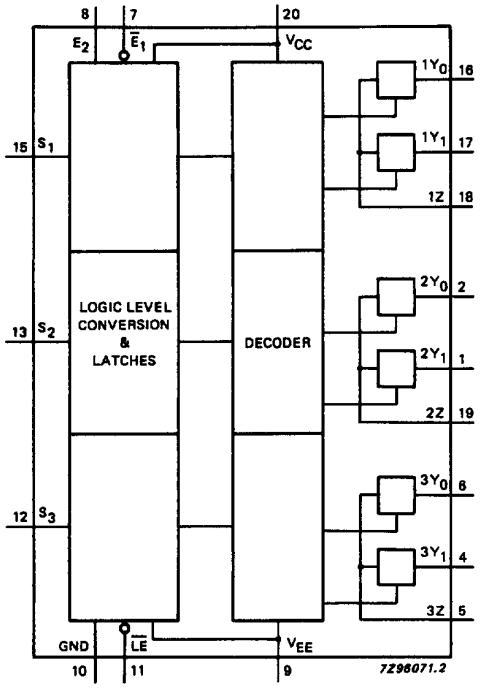


Fig.4 Functional diagram.

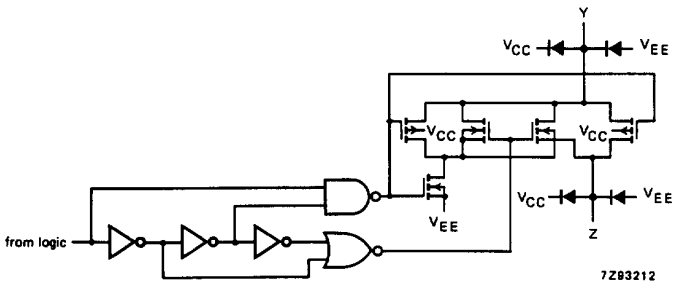


Fig.5 Schematic diagram (one switch).

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)
Voltages are referenced to V_{EE} = GND (ground = 0 V)

SYMBOL	PARAMETER	MIN.	MAX.	UNIT	CONDITIONS
V_{CC}	DC supply voltage	–0.5	+11.0	V	
$\pm I_{IK}$	DC digital input diode current		20	mA	for $V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V
$\pm I_{SK}$	DC switch diode current		20	mA	for $V_S < -0.5$ V or $V_S > V_{CC} + 0.5$ V
$\pm I_S$	DC switch current		25	mA	for -0.5 V $< V_S < V_{CC} + 0.5$ V
$\pm I_{EE}$	DC V_{EE} current		20	mA	
$\pm I_{CC}$; $\pm I_{GND}$	DC V_{CC} or GND current		50	mA	
T_{stg}	storage temperature range	–65	+150	°C	
P_{tot}	power dissipation per package				for temperature range: –40 to +125 °C 74HC/HCT
	plastic DIL		750	mW	above +70 °C: derate linearly with 12 mW/K
	plastic mini-pack (SO)		500	mW	above +70 °C: derate linearly with 8 mW/K
P_S	power dissipation per switch		100	mW	

Note to ratings

1. To avoid drawing V_{CC} current out of terminals nZ, when switch current flows in terminals nY_n, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminals nZ, no V_{CC} current will flow out of terminals nY_n. In this case there is no limit for the voltage drop across the switch, but the voltages at nY_n and nZ may not exceed V_{CC} or V_{EE}.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	74HC			74HCT			UNIT	CONDITIONS
		min.	typ.	max.	min.	typ.	max.		
V_{CC}	DC supply voltage V_{CC}–GND	2.0	5.0	10.0	4.5	5.0	5.5	V	see Figs 6 and 7
V_{CC}	DC supply voltage V_{CC}–V_{EE}	2.0	5.0	10.0	2.0	5.0	10.0	V	see Figs 6 and 7
V_I	DC input voltage range	GND		V_{CC}	GND		V_{CC}	V	
V_S	DC switch voltage range	V_{EE}		V_{CC}	V_{EE}		V_{CC}	V	
T_{amb}	operating ambient temperature range	–40		+85	–40		+85	°C	see DC and AC CHARACTER-ISTICS
T_{amb}	operating ambient temperature range	–40		+125	–40		+125	°C	
t_r, t_f	input rise and fall times		6.0	1000 500 400 250		6.0	500	ns	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V V_{CC} = 10.0 V

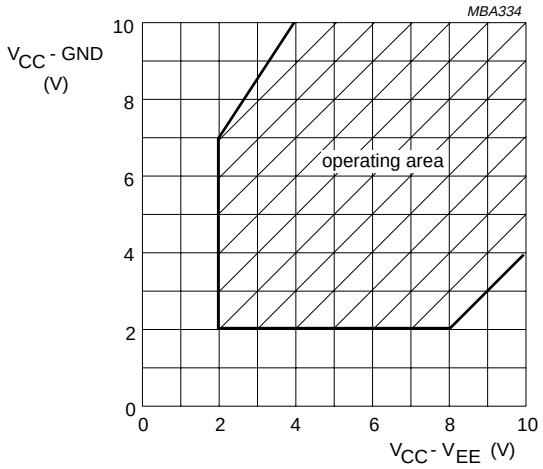


Fig.6 Guaranteed operating area as a function of the supply voltages for 74HC4353.

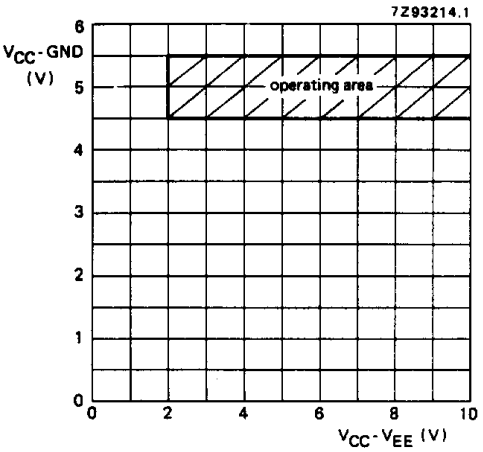


Fig.7 Guaranteed operating area as a function of the supply voltages for 74HCT4353.

DC CHARACTERISTICS FOR 74HC/HCT

For 74HC: V_{CC} – GND or V_{CC} – V_{EE} = 2.0, 4.5, 6.0 and 9.0 V

For 74HCT: V_{CC} – GND = 4.5 and 5.5 V; V_{CC} – V_{EE} = 2.0, 4.5, 6.0 and 9.0 V

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS				
		74HC/HCT								V_{CC} (V)	V_{EE} (V)	I_S (μA)	V_{is}	V_I
		+25			–40 to +85		–40 to +125							
		min.	typ.	max.	min.	max.	min.	max.						
R_{ON}	ON resistance (peak)		–	–		–		–	Ω	2.0	0	100	V_{CC}	V_{IN}
			100	180		225		270	Ω	4.5	0	1000	to	or
			90	160		200		240	Ω	6.0	0	1000	V_{EE}	V_{IL}
			70	130		165		195	Ω	4.5	–4.5	1000		
R_{ON}	ON resistance (rail)		150	–		–		–	Ω	2.0	0	100	V_{EE}	V_{IH}
			80	140		175		210	Ω	4.5	0	1000		or
			70	120		150		180	Ω	6.0	0	1000		V_{IL}
			60	105		130		160	Ω	4.5	–4.5	1000		
R_{ON}	ON resistance		150	–		–		–	Ω	2.0	0	100	V_{CC}	V_{IH}
			90	160		200		240	Ω	4.5	0	1000		or
			80	140		175		210	Ω	6.0	0	1000		V_{IL}
			65	120		150		180	Ω	4.5	–4.5	1000		
ΔR_{ON}	maximum ΔON resistance between any two channels		–						Ω	2.0	0		V_{CC}	V_{IH}
			9						Ω	4.5	0		to	or
			8						Ω	6.0	0		V_{EE}	V_{IL}
			6						Ω	4.5	–4.5			

Notes to DC characteristics

1. At supply voltages (V_{CC} – V_{EE}) approaching 2.0 V the analog switch ON-resistance becomes extremely non-linear. There it is recommended that these devices be used to transmit digital signals only, when using these supply voltages.
2. For test circuit measuring R_{ON} see Fig.8.

DC CHARACTERISTICS FOR 74HC

Voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS			
		74HC								V_{CC} (V)	V_{EE} (V)	V_I	OTHER
		+25			−40 to +85		−40 to +125						
		min.	typ.	max.	min.	max.	min.	max.					
V_{IH}	HIGH level input voltage	1.5 3.15 4.2 6.3	1.2 2.4 3.2 4.7		1.5 3.15 4.2 6.3		1.5 3.15 4.2 6.3		V	2.0 4.5 6.0 9.0			
V_{IL}	LOW level input voltage		0.8 2.1 2.8 4.3	0.5 1.35 1.8 2.7		0.5 1.35 1.8 2.7		0.5 1.35 1.8 2.7	V	2.0 4.5 6.0 9.0			
$\pm I_I$	input leakage current			0.1 0.2		1.0 2.0		1.0 2.0	µA	6.0 10.0	0 0	V_{CC} or GND	
$\pm I_S$	analog switch OFF-state current per channel			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ (see Fig.10)
$\pm I_S$	analog switch OFF-state current all channels			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ (see Fig.10)
$\pm I_S$	analog switch ON-state current			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ (see Fig.11)
I_{CC}	quiescent supply current			8.0 16.0		80.0 160.0		160.0 320.0	µA	6.0 10.0	0 0	V_{CC} or GND	$V_{is} = V_{EE}$ or V_{CC}; $V_{os} = V_{CC}$ or V_{EE}

AC CHARACTERISTICS FOR 74HC

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS		
		74HC										
		+25			−40 to +85		−40 to +125			V_{CC} (V)	V_{EE} (V)	OTHER
		min.	typ.	max.	min.	max.	min.	max.				
t_{PHL}/ t_{PLH}	propagation delay V_{is} to V_{os}		14 5 4 4	60 12 10 8		75 15 13 10		90 18 15 12	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = ∞; C_L = 50 pF (see Fig.18)
t_{PZH}/ t_{PZL}	turn “ON” time $\overline{E}_1$; E_2 to V_{os}		61 22 18 18	250 50 43 40		315 63 54 50		375 75 64 60	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PZH}/ t_{PZL}	turn “ON” time $\overline{LE}$ to V_{os}		55 20 16 17	200 40 34 40		250 50 43 50		300 60 51 60	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PZH}/ t_{PZL}	turn “ON” time S_n to V_{os}		61 22 18 17	225 45 38 40		280 56 48 50		340 68 58 60	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time $\overline{E}_1$; E_2 to V_{os}		66 24 19 19	250 50 43 40		315 63 54 50		375 75 64 60	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time S_n to V_{os}; $\overline{LE}$ to V_{os}		55 20 16 19	200 40 34 40		250 50 43 50		300 60 51 60	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{su}	set-up time S_n to $\overline{LE}$	60 12 10 18	17 6 5 8		75 15 13 23		90 18 15 27		ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)
t_h	hold time S_n to $\overline{LE}$	5 5 5 5	−6 −2 −2 −3		5 5 5 5		5 5 5 5		ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)
t_W	$\overline{LE}$ minimum pulse width HIGH	80 16 14 16	11 4 3 6		100 20 17 20		120 24 20 24		ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)

DC CHARACTERISTICS FOR 74HCT

Voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS			
		74HCT								V_{CC} (V)	V_{EE} (V)	V_I	OTHER
		+25			−40 to +85		−40 to +125						
		min.	typ.	max.	min.	max.	min.	max.					
V_{IH}	HIGH level input voltage	2.0	1.6		2.0		2.0		V	4.5 to 5.5			
V_{IL}	LOW level input voltage		1.2	0.8		0.8		0.8	V	4.5 to 5.5			
$\pm I_I$	input leakage current			0.1		1.0		1.0	µA	5.5	0	V_{CC} or GND	
$\pm I_S$	analog switch OFF-state current per channel			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ Fig.10
$\pm I_S$	analog switch OFF-state current all channels			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ Fig.10
$\pm I_S$	analog switch ON-state current			0.1		1.0		1.0	µA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ Fig.11
I_{CC}	quiescent supply current			8.0 16.0		80.0 160.0		160.0 320.0	µA	5.5 5.0	0 −5.0	V_{CC} or GND	$V_{is} = V_{EE}$ or V_{CC}; $V_{os} = V_{CC}$ or V_{EE}
ΔI_{CC}	additional quiescent supply current per input pin for unit load coefficient is 1 (note 1)		100	360		450		490	µA	4.5 to 5.5	0	V_{CC} −2.1 V	other inputs at V_{CC} or GND

Note to HCT types

1. The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given here. To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

INPUT	UNIT LOAD COEFFICIENT
$\overline{E}_1$, E_2	0.50
S_n	0.50
$\overline{LE}$	1.5

AC CHARACTERISTICS FOR 74HCT

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS		
		74HCT								V_{CC} (V)	V_{EE} (V)	OTHER
		+25			−40 to +85		−40 to +125					
		min.	typ.	max.	min.	max.	min.	max.				
t_{PHL}/ t_{PLH}	propagation delay V_{is} to V_{os}		5 4	12 8		15 10		18 12	ns	4.5 4.5	0 −4.5	$R_L = \infty$; C_L = 50 pF (see Fig.18)
t_{PZH}/ t_{PZL}	turn “ON” time $\overline{E}_1$ to V_{os}		26 22	55 45		69 56		83 68	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PZH}/ t_{PZL}	turn “ON” time E_2 to V_{os}		22 18	50 40		63 50		75 60	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PZH}/ t_{PZL}	turn “ON” time $\overline{LE}$ to V_{os}		21 17	45 40		56 50		68 60	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PZH}/ t_{PZL}	turn “ON” time S_n to V_{os}		25 19	50 45		63 56		75 68	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time $\overline{E}_1$ to V_{os}		23 19	50 40		63 50		75 60	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time E_2 to V_{os}		27 23	50 40		63 50		75 60	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time $\overline{LE}$ to V_{os}		19 19	40 40		50 50		60 60	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{PHZ}/ t_{PLZ}	turn “OFF” time S_n to V_{os}		22 22	45 45		56 56		68 68	ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.19)
t_{su}	set-up time S_n to $\overline{LE}$	12 15	7 9		15 19		18 22		ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)
t_h	hold time S_n to $\overline{LE}$	5 5	0 −2		5 5		5 5		ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)
t_W	$\overline{LE}$ minimum pulse width HIGH	16 16	3 5		20 20		24 24		ns	4.5 4.5	0 −4.5	R_L = 1 kΩ; C_L = 50 pF (see Fig.20)

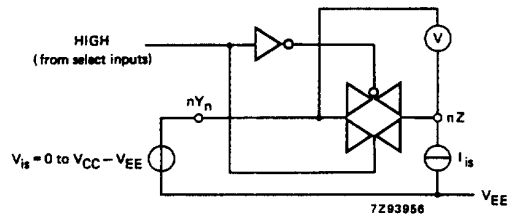


Fig.8 Test circuit for measuring R_{ON}.

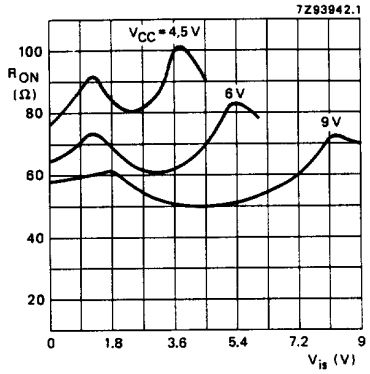


Fig.9 Typical R_{ON} as a function of input voltage V_{is} for V_{is} = 0 to $V_{CC} - V_{EE}$.

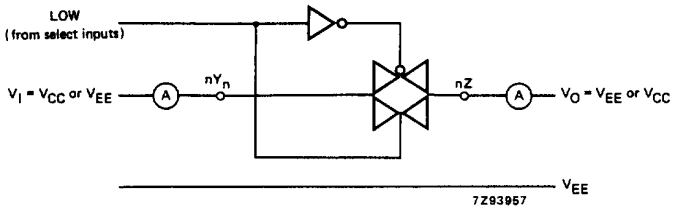


Fig.10 Test circuit for measuring OFF-state current.

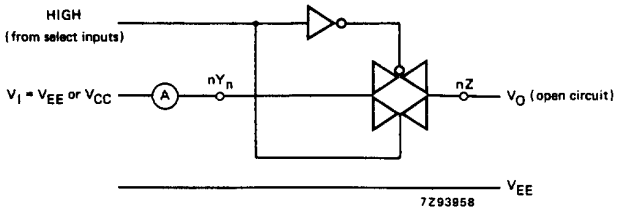


Fig.11 Test circuit for measuring ON-state current.

ADDITIONAL AC CHARACTERISTICS FOR 74HC/HCT

Recommended conditions and typical values

GND = 0 V; T_{amb} = 25 °C

SYMBOL	PARAMETER	typ.	UNIT	V_{CC} (V)	V_{EE} (V)	$V_{is(p-p)}$ (V)	CONDITIONS
	sine-wave distortion f = 1 kHz	0.04 0.02	% %	2.25 4.5	–2.25 –4.5	4.0 8.0	R_L = 10 kΩ; C_L = 50 pF (see Fig.14)
	sine-wave distortion f = 10 kHz	0.12 0.06	% %	2.25 4.5	–2.25 –4.5	4.0 8.0	R_L = 10 kΩ; C_L = 50 pF (see Fig.14)
	switch “OFF” signal feed-through	–50 –50	dB dB	2.25 4.5	–2.25 –4.5	note 1	R_L = 600 Ω; C_L = 50 pF f = 1 MHz (see Figs 12 and 15)
	crosstalk between any two switches/ multiplexers	–60 –60	dB dB	2.25 4.5	–2.25 –4.5	note 1	R_L = 600 Ω; C_L = 50 pF; f = 1 MHz (see Fig.16)
$V_{(p-p)}$	crosstalk voltage between control and any switch (peak-to-peak value)	110 220	mV mV	4.5 4.5	0 –4.5		R_L = 600 Ω; C_L = 50 pF; f = 1 MHz ($\overline{E}_1$, E_2 or S_n, square-wave between V_{CC} and GND, $t_r = t_f$ = 6 ns) (see Fig.17)
f_{max}	minimum frequency response (–3dB)	160 170	MHz MHz	2.25 4.5	–2.25 –4.5	note 2	R_L = 50 Ω; C_L = 10 pF (see Figs 13 and 14)
C_S	maximum switch capacitance independent (Y) common (Z)	 5 12	 pF pF				

Notes to the AC characteristics

1. Adjust input voltage V_{is} to 0 dBm level (0 dBm = 1 mW into 600 Ω).
2. Adjust input voltage V_{is} to 0 dBm level at V_{os} for 1 MHz (0 dBm = 1 mW into 50 Ω).

General note

V_{is} is the input voltage at an nY_n or nZ terminal, whichever is assigned as an input.
V_{os} is the output voltage at an nY_n or nZ terminal, whichever is assigned as an output.

Test conditions:
V_{CC} = 4.5 V; GND = 0 V; V_{EE} = – 4.5 V;
R_L = 50 Ω; R_{source} = 1 kΩ.

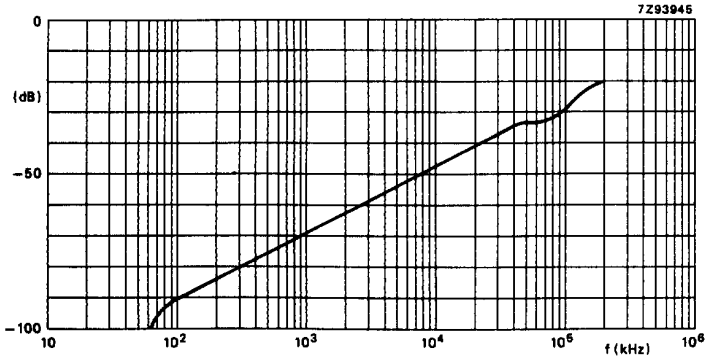


Fig.12 Typical switch “OFF” signal feed-through as a function of frequency.

Test conditions:
V_{CC} = 4.5 V; GND = 0 V; V_{EE} = – 4.5 V;
R_L = 50 Ω; R_{source} = 1 kΩ.

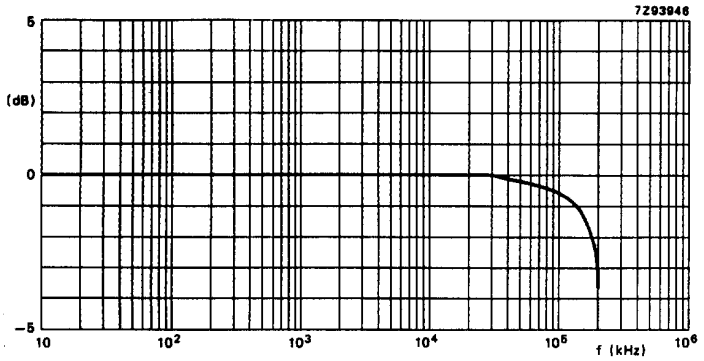


Fig.13 Typical frequency response.

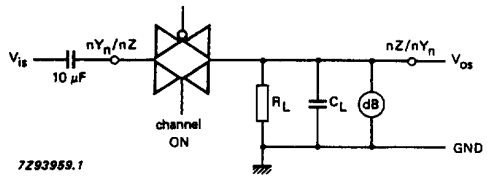


Fig.14 Test circuit for measuring sine-wave distortion and minimum frequency response.

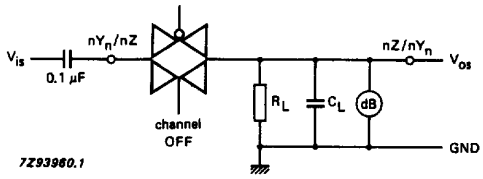
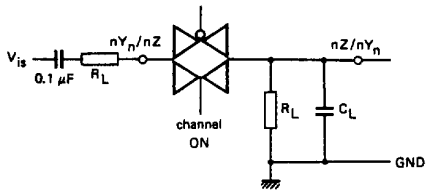
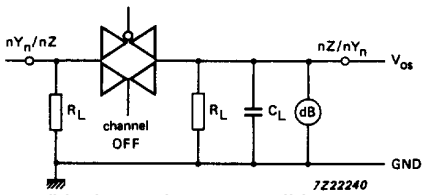


Fig.15 Test circuit for measuring switch “OFF” signal feed-through.

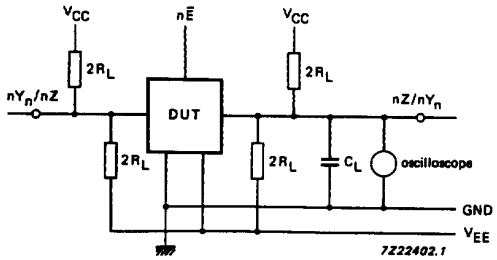


(a) = channel ON condition



(b) channel OFF condition.

Fig.16 Test circuits for measuring crosstalk between any two switches/multiplexers.



The crosstalk is defined as follows (oscilloscope output):

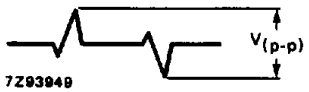


Fig.17 Test circuit for measuring crosstalk between control and any switch.

AC WAVEFORMS

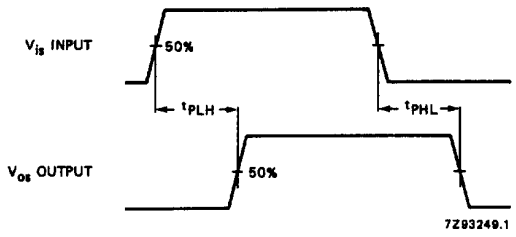
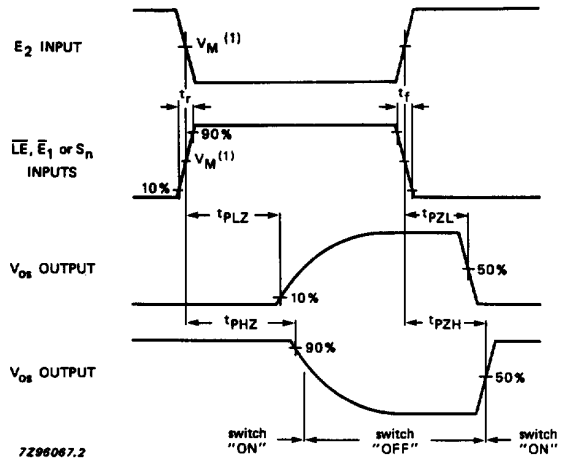
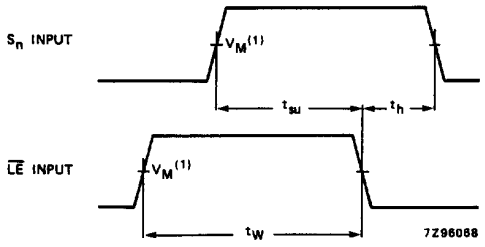


Fig.18 Waveforms showing the input (V_{is}) to output (V_{os}) propagation delays.



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT : V_M = 1.3 V; V_I = GND to 3 V.

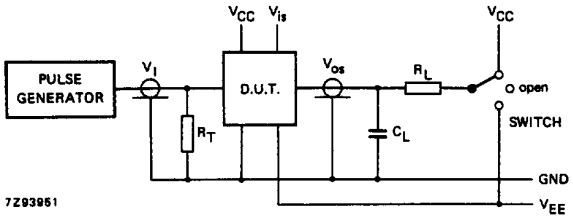
Fig.19 Waveforms showing the turn-ON and turn-OFF times.



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT : V_M = 1.3 V; V_I = GND to 3 V.

Fig.20 Waveforms showing the set-up and hold times from S_n inputs to $\overline{LE}$ input, and minimum pulse width of $\overline{LE}$.

TEST CIRCUIT AND WAVEFORMS



Conditions

TEST	SWITCH	V_{is}
t_{PZH}	V_{EE}	V_{CC}
t_{PZL}	V_{CC}	V_{EE}
t_{PHZ}	V_{EE}	V_{CC}
t_{PLZ}	V_{CC}	V_{EE}
others	open	pulse

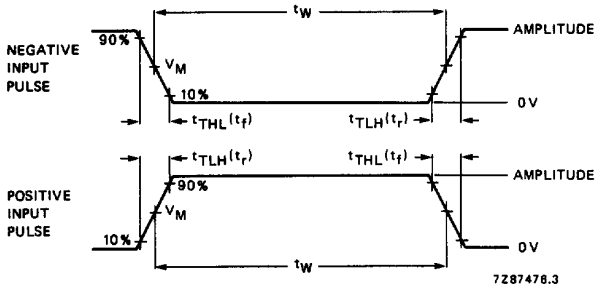
FAMILY	AMPLITUDE	V_M	t_r; t_f	
			f_{max}; PULSE WIDTH	OTHER
74HC	V_{CC}	50%	< 2 ns	6 ns
74HCT	3.0 V	1.3 V	< 2 ns	6 ns

C_L = load capacitance including jig and probe capacitance (see AC CHARACTERISTICS for values).

R_T = termination resistance should be equal to the output impedance Z_O of the pulse generator.

t_r = t_f = 6 ns; when measuring f_{max}, there is no constraint on t_r, t_f with 50% duty factor.

Fig.21 Test circuit for measuring AC performance.



Conditions

TEST	SWITCH	V_{is}
t_{PZH}	V_{EE}	V_{CC}
t_{PZL}	V_{CC}	V_{EE}
t_{PHZ}	V_{EE}	V_{CC}
t_{PLZ}	V_{CC}	V_{EE}
others	open	pulse

FAMILY	AMPLITUDE	V_M	t_r; t_f	
			f_{max}; PULSE WIDTH	OTHER
74HC	V_{CC}	50%	< 2 ns	6 ns
74HCT	3.0 V	1.3 V	< 2 ns	6 ns

C_L = load capacitance including jig and probe capacitance (see AC CHARACTERISTICS for values).

R_T = termination resistance should be equal to the output impedance Z_O of the pulse generator.

t_r = t_f = 6 ns; when measuring f_{max}, there is no constraint on t_r, t_f with 50% duty factor.

Fig.22 Input pulse definitions.

PACKAGE OUTLINES

See *"74HC/HCT/HCU/HCMOS Logic Package Outlines"*.